

SK10GD126ET



SEMITOP® 3

IGBT Module

SK10GD126ET

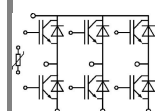
Preliminary Data

Features

- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- Ultrafast NPT technology IGBT
- CAL technology FWD
- Integrated NTC temperature sensor

Typical Applications*

- Inverter

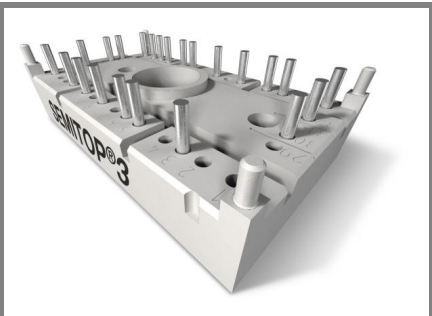


GD-ET

Absolute Maximum Ratings			$T_s = 25\text{ }^{\circ}\text{C}$, unless otherwise specified	
Symbol	Conditions		Values	Units
IGBT				
V_{CES}	$T_j = 25\text{ }^{\circ}\text{C}$		1200	V
I_C	$T_j = 150\text{ }^{\circ}\text{C}$	$T_s = 25\text{ }^{\circ}\text{C}$	15	A
		$T_s = 80\text{ }^{\circ}\text{C}$	11	A
I_{CRM}	$I_{CRM} = 2 \times I_{Cnom}$		16	A
V_{GES}			± 20	V
t_{psc}	$V_{CC} = 600\text{ V}$; $V_{GE} \leq 20\text{ V}$; $T_j = 125\text{ }^{\circ}\text{C}$ $V_{CES} < 1200\text{ V}$		10	μs
Inverse Diode				
I_F	$T_j = 150\text{ }^{\circ}\text{C}$	$T_s = 25\text{ }^{\circ}\text{C}$	25	A
		$T_s = 80\text{ }^{\circ}\text{C}$	17	A
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$		30	A
Module				
$I_{t(RMS)}$				A
T_{vj}			-40 ... +150	$^{\circ}\text{C}$
T_{stg}			-40 ... +125	$^{\circ}\text{C}$
V_{isol}	AC, 1 min.		2500	V

Characteristics			T _s = 25 °C, unless otherwise specified			
Symbol	Conditions		min.	typ.	max.	Units
IGBT						
V _{GE(th)}	V _{GE} = V _{CE} , I _C = 0,3 mA		5	5,8	6,5	V
I _{CES}	V _{GE} = 0 V, V _{CE} = V _{CES} T _j = 25 °C T _j = 125 °C				0,05	mA mA
I _{GES}	V _{CE} = 0 V, V _{GE} = 20 V T _j = 25 °C T _j = 125 °C				120	nA nA
V _{CE0}				T _j = 25 °C T _j = 125 °C	1 1,2	V V
r _{CE}	V _{GE} = 15 V T _j = 25 °C T _j = 125 °C			87 138	113	mΩ mΩ
V _{CE(sat)}	I _{Cnom} = 8 A, V _{GE} = 15 V T _j = 25 °C _{chiplev.} T _j = 125 °C _{chiplev.}			1,7 2,2	2,1	V V
C _{ies} C _{oes} C _{res}	V _{CE} = 25, V _{GE} = 0 V f = 1 MHz			0,6 0,037 0,029		nF nF nF
t _{d(on)} t _r E _{on}	R _{Gon} = 75 Ω	V _{CC} = 600V I _C = 8A		85 30 1		ns ns mJ
t _{d(off)} t _f E _{off}	R _{Goff} = 75 Ω	T _j = 125 °C V _{GE} = ±15V		430 90 1		ns ns mJ
R _{th(j-s)}	per IGBT				2	K/W

SK10GD126ET



SEMITOP[®] 3

IGBT Module

SK10GD126ET

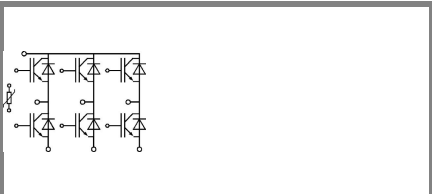
Preliminary Data

Features

- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- Ultrafast NPT technology IGBT
- CAL technology FWD
- Integrated NTC temperature sensor

Typical Applications*

- Inverter

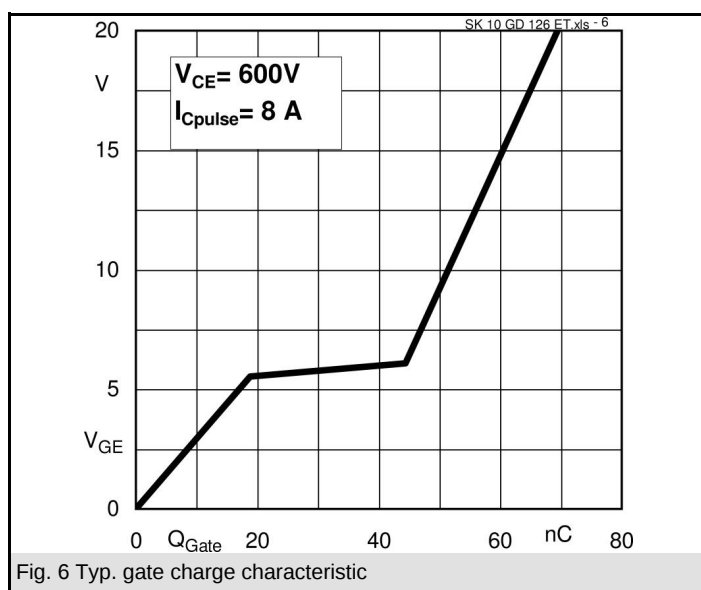
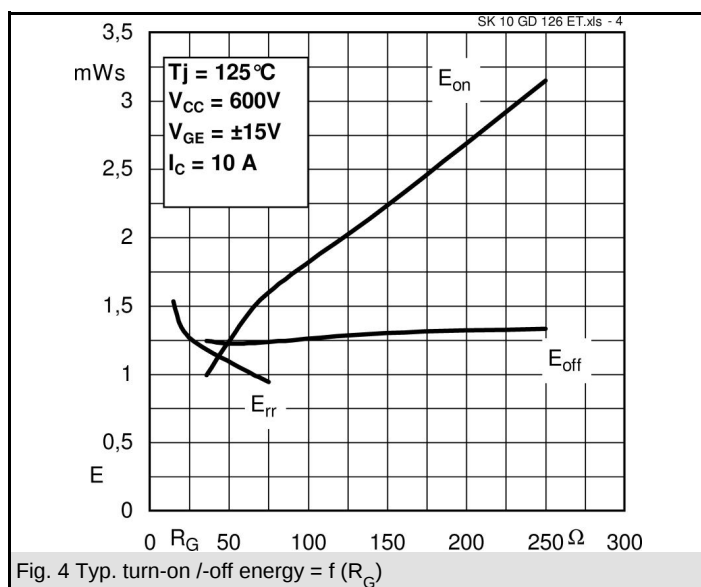
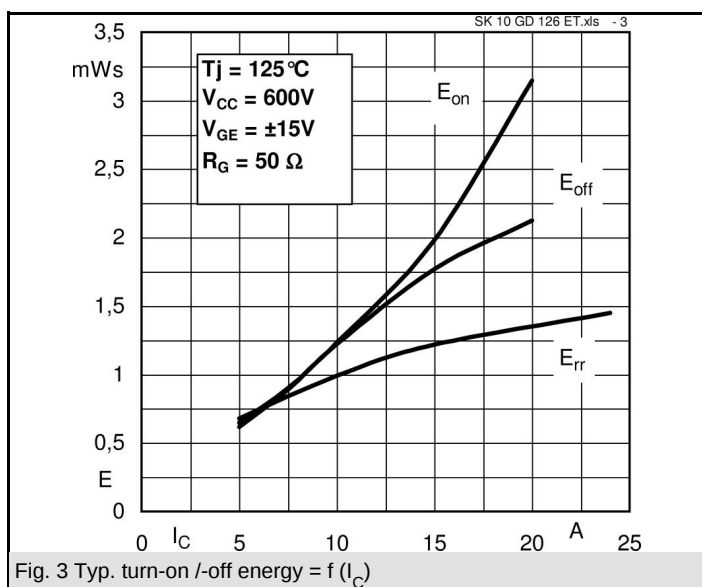
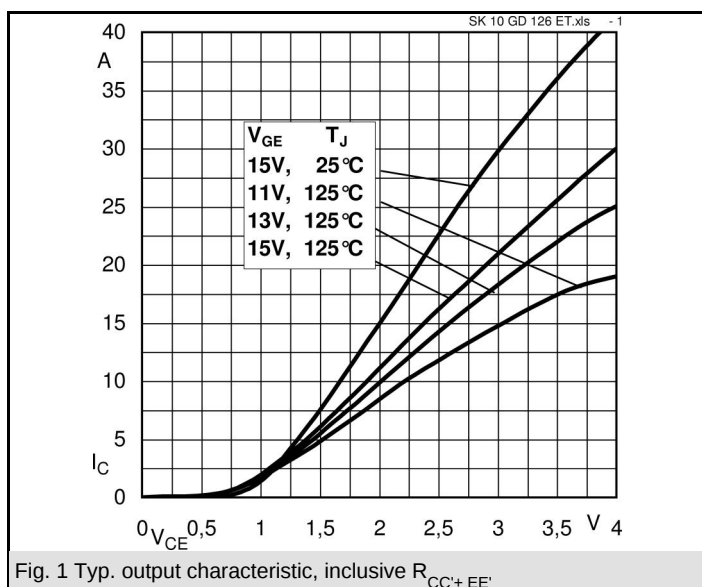


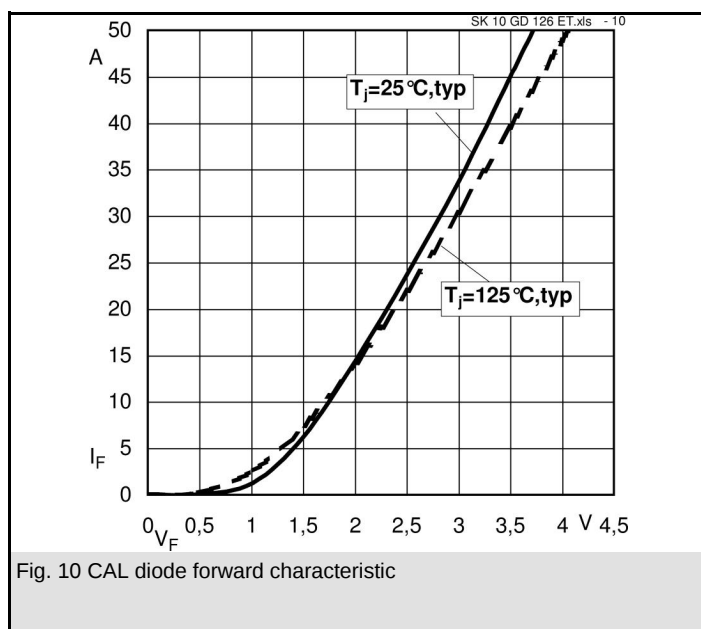
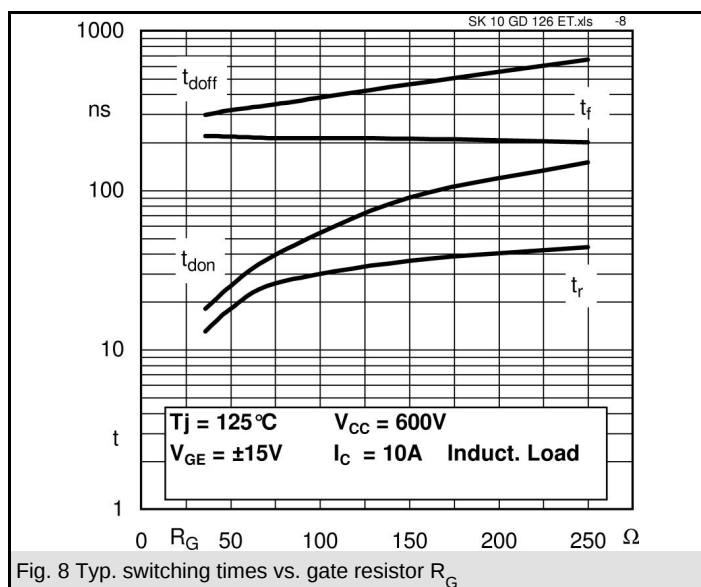
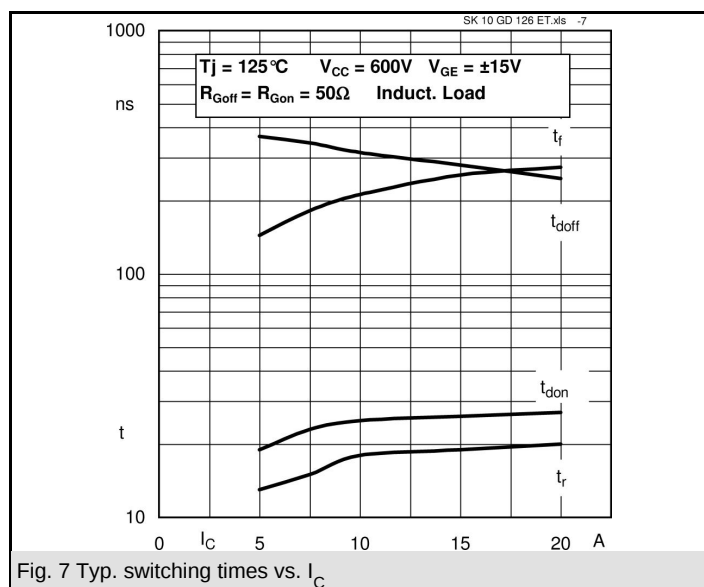
GD-ET

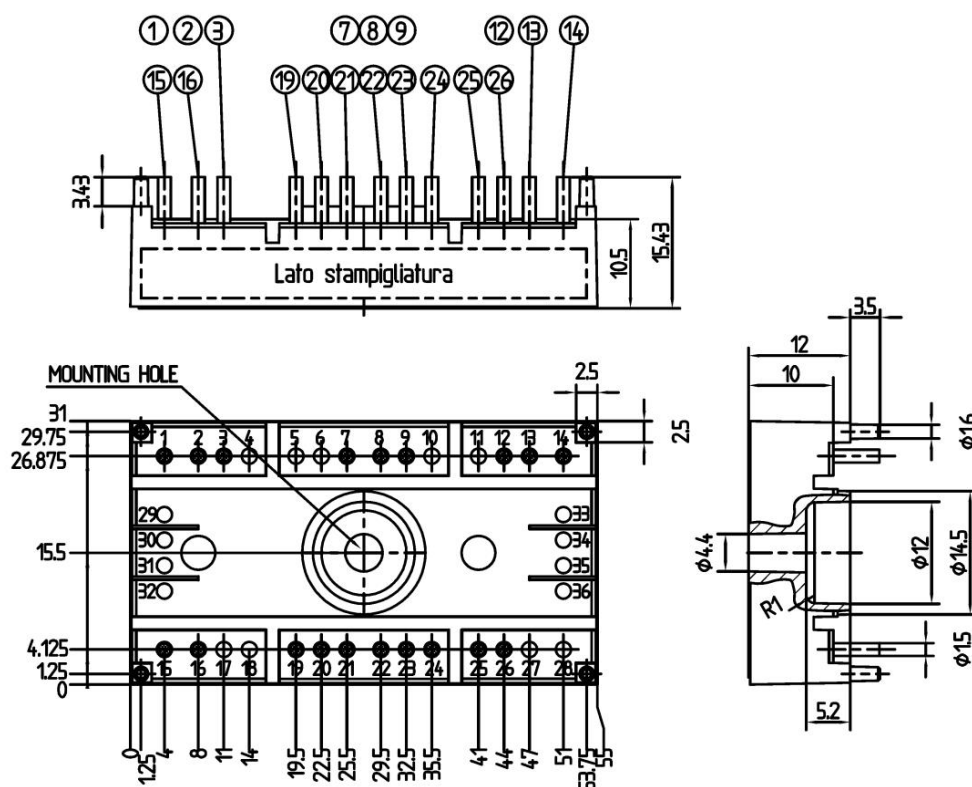
Characteristics					
Symbol	Conditions	min.	typ.	max.	Units
Inverse Diode					
$V_F = V_{EC}$	$I_{Fnom} = 8\text{ A}; V_{GE} = 0\text{ V}$		$T_j = 25\text{ }^{\circ}\text{C}_{chiplev.}$	1,9	2,2
			$T_j = 125\text{ }^{\circ}\text{C}_{chiplev.}$	2	V
V_{F0}			$T_j = 25\text{ }^{\circ}\text{C}$	1	1,1
			$T_j = 125\text{ }^{\circ}\text{C}$	0,8	0,9
r_F			$T_j = 25\text{ }^{\circ}\text{C}$	40	47
			$T_j = 125\text{ }^{\circ}\text{C}$	53	mΩ
I_{RRM}	$I_F = 15\text{ A}$		$T_j = 125\text{ }^{\circ}\text{C}$	21	A
Q_{rr}	$di/dt = -300\text{ A}/\mu\text{s}$			3,5	μC
E_{rr}	$V_{CC} = 600\text{ V}$			1,4	mJ
$R_{th(j-s)D}$	per diode			2,1	K/W
M_s	to heat sink	2,25		2,5	Nm
w			30		g
Temperature sensor					
R_{100}	$T_s = 100^{\circ}\text{C}$ ($R_{25} = 5\text{ k}\Omega$)		493±5%		Ω

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

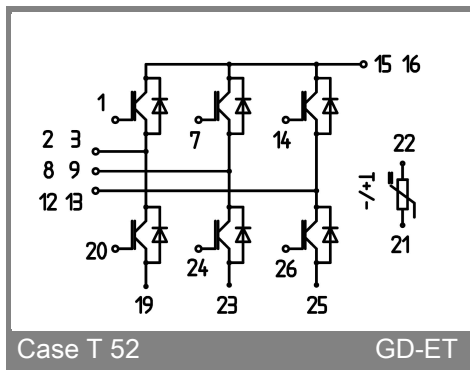
* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.







Case T52 (Suggested hole diameter, in the PCB, for solder pins and plastic mounting pins: 2mm)



Case T 52

GD-ET